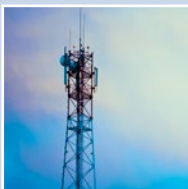
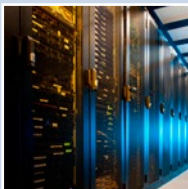




650V thinQ!™ SiC Diodes Generation 5

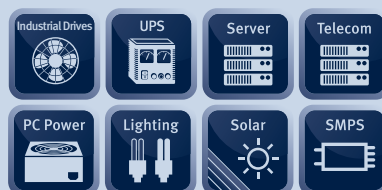
Your Way is our Way: Improve Efficiency and Solution Costs



With the 5th generation of SiC Schottky Barrier Diodes Infineon delivers market leading efficiency at an attractive price/performance ratio. Infineon's proprietary diffusion soldering process is now combined with a new, more compact design as well as latest advancements in thin wafer technology bringing improved thermal characteristics and lower Figures of Merit ($Q_c \times V_f$).

Key features and benefits of Generation 5 thinQ!™ SiC Diodes

- Improved Efficiency over all load conditions with respect to previous thinQ!™ generations
- V_{br} increased from 600V to 650V, complementing our 650V CoolMOS™ offer
- Temperature independent switching behavior for highly stable switching performance
- High operating temperature (T_j max 175°C)
- Soft switching reverse recovery waveform leading to low EMI levels



For further information please visit our website:
www.infineon.com/sic-gen5

